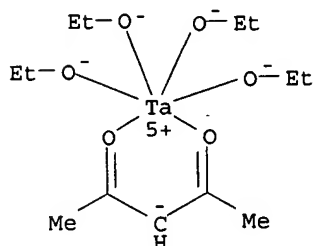


L15 ANSWER 12 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN  
 AN 1995:995408 HCAPLUS  
 DN 124:133984  
 TI Tantalum compounds  
 IN Leedham, Timothy John; Drake, Simon Robert  
 PA UK  
 SO PCT Int. Appl., 37 pp.  
 CODEN: PIXXD2  
 DT Patent  
 LA English  
 IC ICM C07F009-00  
 ICS C23C016-40  
 CC 78-7 (Inorganic Chemicals and Reactions)  
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 9526355	A1	19951005	WO 1995-GB644	19950323
	W: AM, AT, AU, BB, BG, BR, BY, CA, CH, CN, CZ, DE, DK, EE, ES, FI, GB, GE, HU, IS, JP, KE, KG, KP, KR, KZ, LK, LR, LT, LU, LV, MD, MG, MN, MW, MX, NL, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, TJ, TT				
	RW: KE, MW, SD, SZ, UG, AT, BE, CH, DE, DK, ES, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, BF, BJ, CF, CG, CI, CM, GA, GN, ML, MR, NE, SN, TD, TG				
	AU 9519553	A1	19951017	AU 1995-19553	19950323
PRAI	GB 1994-6060		19940326		
	GB 1994-23750		19941124		
	WO 1995-GB644		19950323		
AB	Ta(OR) <sub>5</sub> -nXn (n = 1, 2 or 3; each R is independently selected from a straight or branched chain alkyl group having between 1 and 4 C atoms, or SiMe <sub>3</sub> ; and X is a bidentate ligand) were prepd. These compds. may be used as precursors for metal org. CVD (MOCVD) of oxide layers in applications such as integrated circuit dielects., microwaves, optical coatings and catalysts.				
	RL: IMF (Industrial manufacture); RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent) (prepn. and use in MOCVD for prepn. of tantalum oxide)				
RN	20219-33-4 HCAPLUS				
CN	Tantalum, tetraethoxy(2,4-pentanedionato-.kappa.O,.kappa.O')-, (OC-6-22)-(9CI) (CA INDEX NAME)				

→ See chem  
structure  
on  
next sheet.



RN 172901-18-7 HCAPLUS  
 CN Tantalum, tetraethoxy[2-(methoxy-.kappa.O)ethanolato-.kappa.O]-, (OC-6-33)-(9CI) (CA INDEX NAME)

on  
next sheet